

**30V DUAL N-CHANNEL ENHANCEMENT MODE MOSFET**
**Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> MAX	I <sub>D</sub> MAX T <sub>A</sub> = +25°C
30V	35mΩ @ V <sub>GS</sub> = 10V	5.5A
	45mΩ @ V <sub>GS</sub> = 4.5V	4.9A

**Description**

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

**Applications**

- DC Motor Control
- DC-AC Inverters

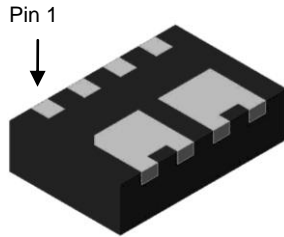
**Features**

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

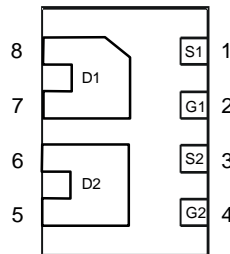
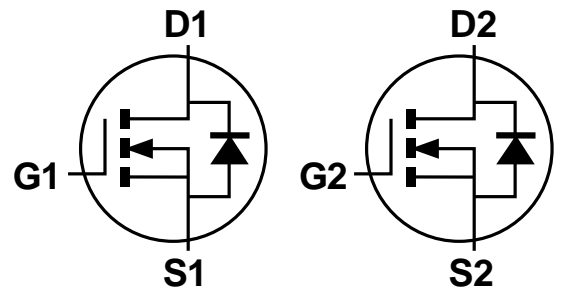
**Mechanical Data**

- Case: V-DFN3020-8 (Type N)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – NiPdAu Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 <sup>(e4)</sup>
- Weight: 0.011 grams (Approximate)

V-DFN3020-8 (Type N)



Bottom View


 Bottom View  
Pin Configuration


Q1 N-Channel MOSFET

Q2 N-Channel MOSFET

Equivalent Circuit

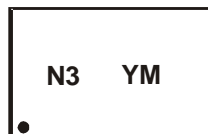
**Ordering Information** (Note 4)

Part Number	Case	Packaging
DMN3035LWN-7	V-DFN3020-8 (Type N)	3,000/Tape & Reel
DMN3035LWN-13	V-DFN3020-8 (Type N)	10,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html).

**Marking Information**

V-DFN3020-8 (Type N)



N3 = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: D = 2016)  
 M = Month (ex: 9 = September)

## Date Code Key

Year	2016	2017	2018	2019	2020	2021	2022	2023
Code	D	E	F	G	H	I	J	K

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V <sub>DSS</sub>	30	V		
Gate-Source Voltage	V <sub>GSS</sub>	±20	V		
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	I <sub>D</sub>	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	5.5 4.4	A
		Maximum Continuous Body Diode Forward Current (Note 6)	I <sub>S</sub>	1	A
Pulsed Drain Current	I <sub>DM</sub>	30	A		
Avalanche Current (Note 7) L = 0.1mH	I <sub>AS</sub>	13	A		
Avalanche Energy (Note 7) L = 0.1mH	E <sub>AS</sub>	9.0	mJ		

**Thermal Characteristics**

Characteristic	Symbol	Value	Units	
Total Power Dissipation (Note 5)	P <sub>D</sub>	T <sub>A</sub> = +25°C	0.77	W
		T <sub>A</sub> = +70°C	0.49	
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	Steady State	162	°C/W
		t < 10s	116	
Total Power Dissipation (Note 6)	P <sub>D</sub>	T <sub>A</sub> = +25°C	1.78	W
		T <sub>A</sub> = +70°C	1.10	
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>θJA</sub>	Steady State	71	°C/W
		t < 10s	50	
Thermal Resistance, Junction to Case (Note 6)	R <sub>θJC</sub>	10.7	°C/W	
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 8)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	—	—	1.0	μA	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 8)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1.0	—	2.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	26	35	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 4.8A
		—	34	45	mΩ	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 4.3A
Diode Forward Voltage	V <sub>SD</sub>	—	0.75	1.1	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1A
<b>DYNAMIC CHARACTERISTICS (Note 9)</b>						
Input Capacitance	C <sub>iss</sub>	—	399	—	pF	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	57	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	50	—	pF	
Gate Resistance	R <sub>g</sub>	—	1.36	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>g</sub>	—	4.5	—	nC	V <sub>DS</sub> = 15V, I <sub>D</sub> = 5.8A
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>g</sub>	—	9.9	—	nC	
Gate-Source Charge	Q <sub>gs</sub>	—	1.2	—	nC	
Gate-Drain Charge	Q <sub>gd</sub>	—	1.8	—	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	—	3.0	—	ns	V <sub>DD</sub> = 15V, V <sub>GS</sub> = 10V, R <sub>L</sub> = 2.6Ω, R <sub>G</sub> = 3Ω
Turn-On Rise Time	t <sub>R</sub>	—	3.3	—	ns	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	10.6	—	ns	
Turn-Off Fall Time	t <sub>F</sub>	—	2.0	—	ns	
Reverse Recovery Time	t <sub>RR</sub>	—	7.9	—	ns	
Reverse Recovery Charge	Q <sub>RR</sub>	—	2.4	—	nC	I <sub>F</sub> = 4.8A, di/dt = 100A/μs

- Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
  7. I<sub>AS</sub> and E<sub>AS</sub> rating are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.
  8. Short duration pulse test used to minimize self-heating effect.
  9. Guaranteed by design. Not subject to product testing.

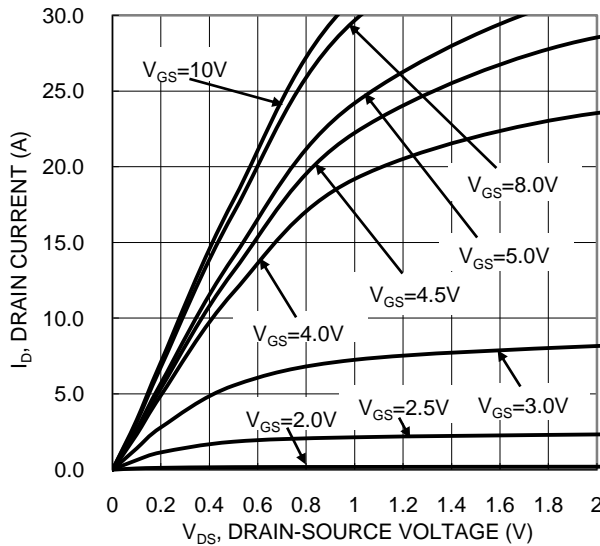


Figure 1. Typical Output Characteristic

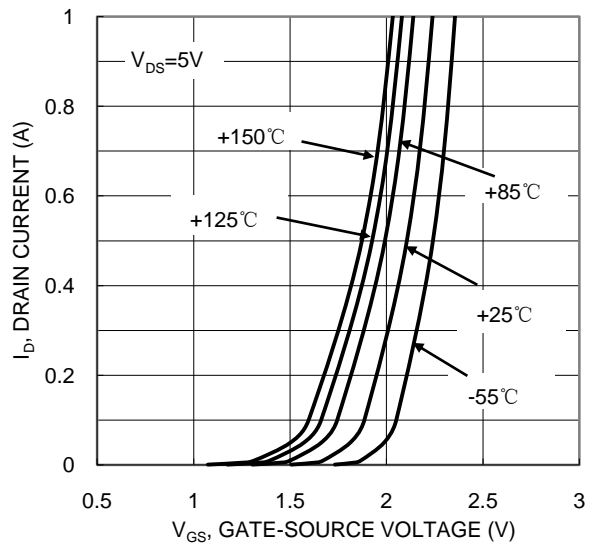


Figure 2. Typical Transfer Characteristic

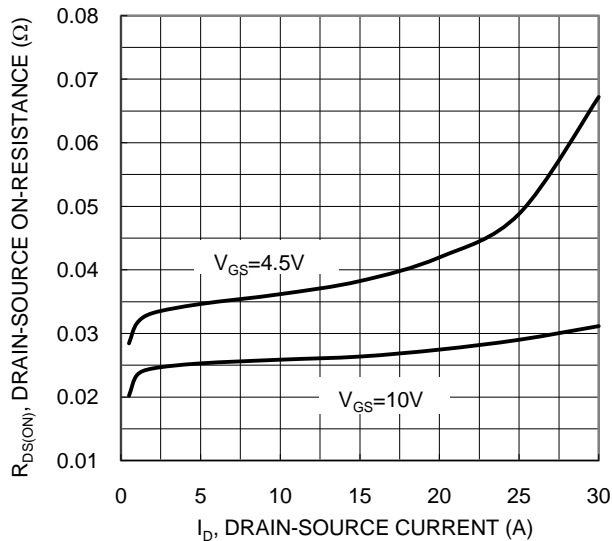


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

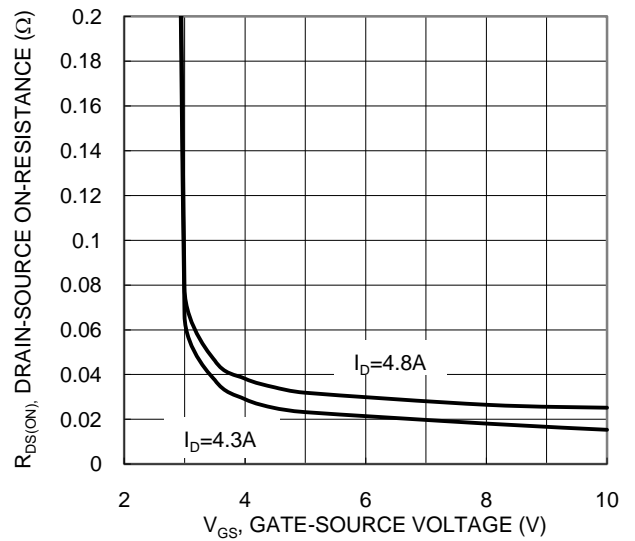


Figure 4. Typical Transfer Characteristic

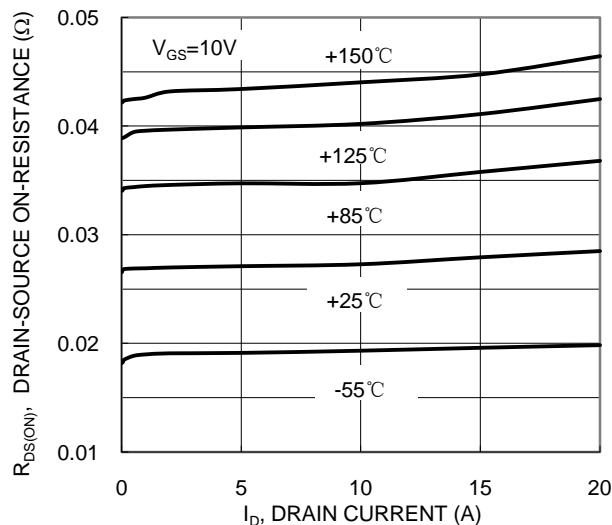


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

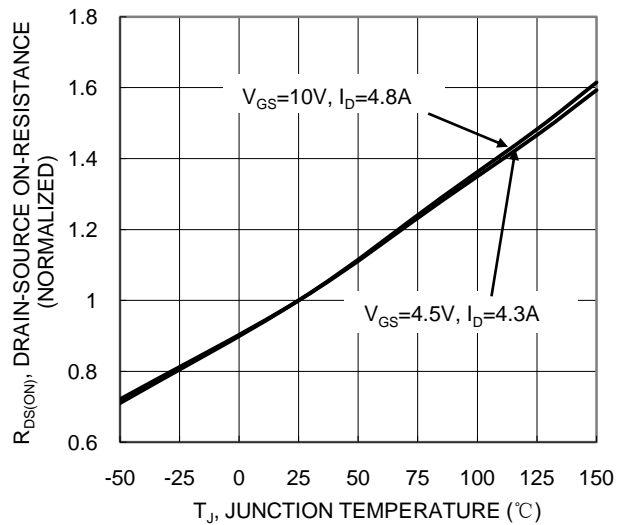


Figure 6. On-Resistance Variation with Temperature

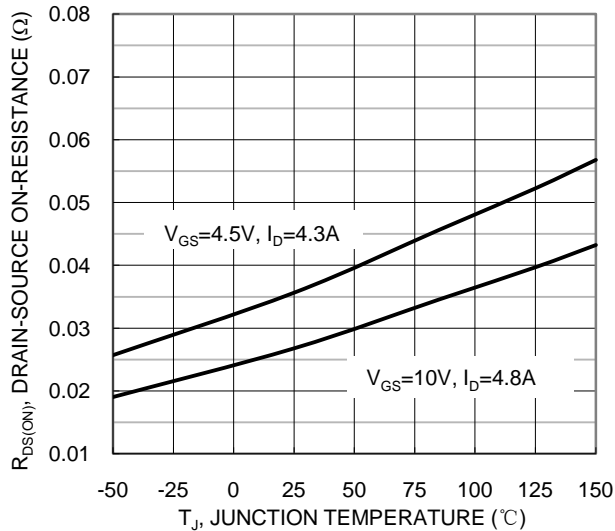


Figure 7. On-Resistance Variation with Temperature

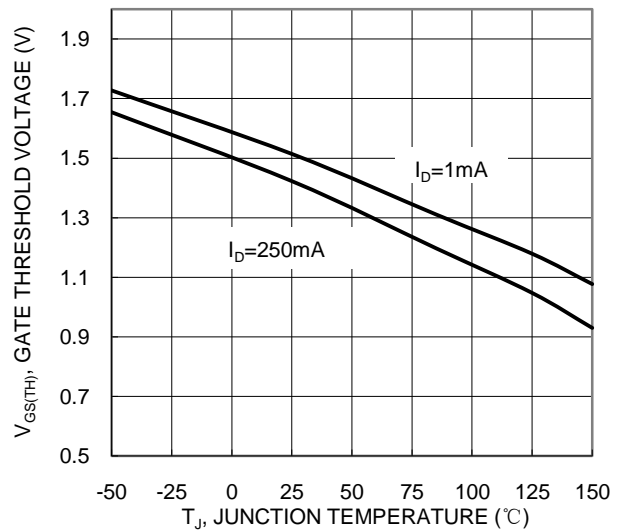


Figure 8. Gate Threshold Variation vs Junction Temperature

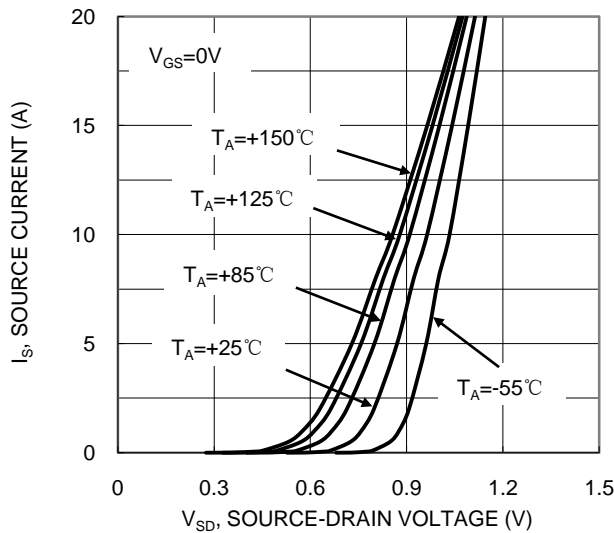


Figure 9. Diode Forward Voltage vs. Current

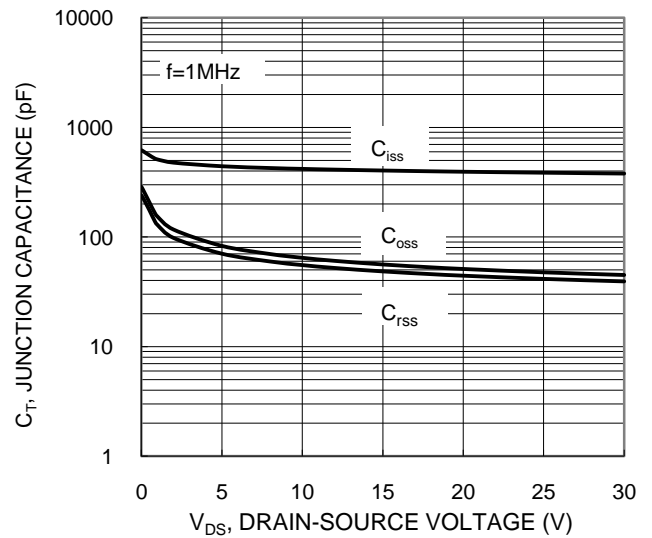


Figure 10. Typical Junction Capacitance

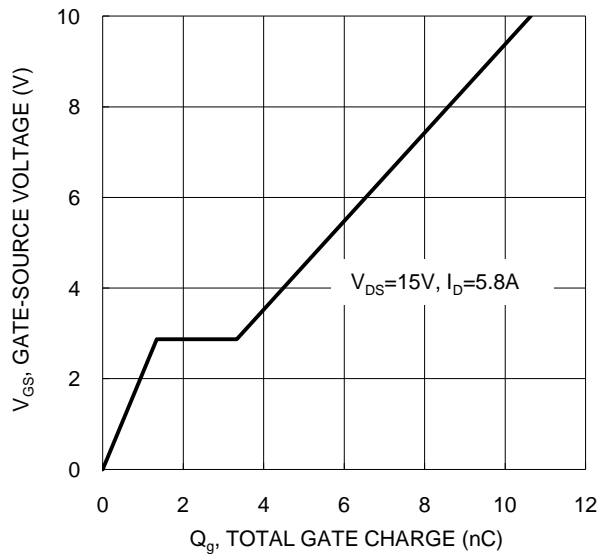


Figure 11. Gate Charge

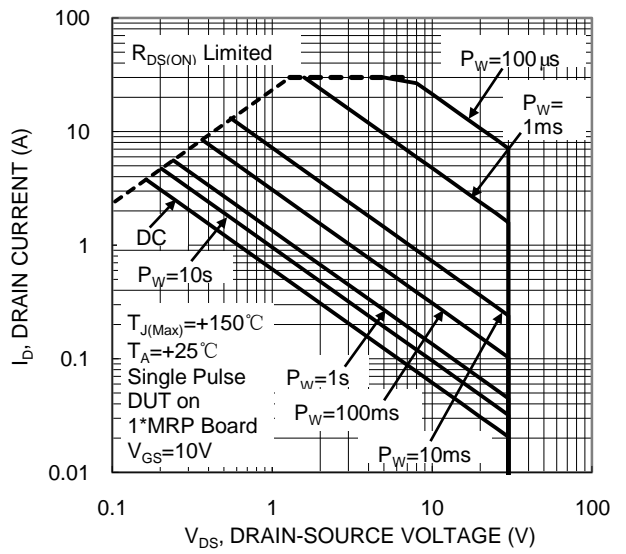


Figure 12. SOA, Safe Operation Area

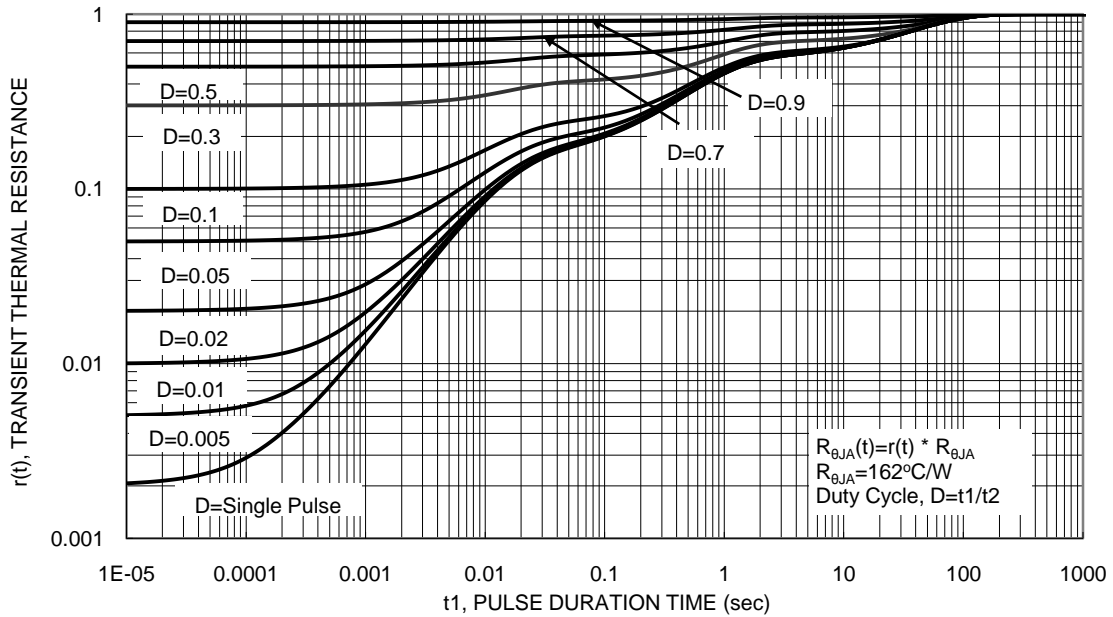
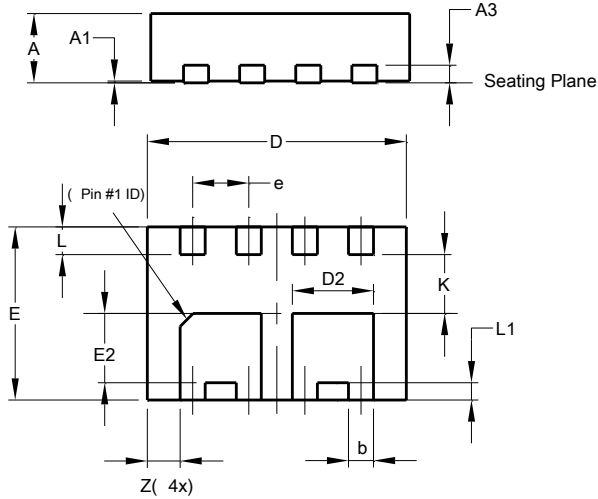


Figure 13 Transient Thermal Resistance

## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

### V-DFN3020-8 (Type N)

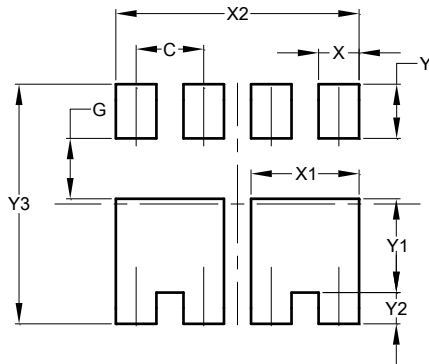


V-DFN3020-8 (Type N)			
Dim	Min	Max	Typ
A	0.77	0.83	0.80
A1	0	0.05	0.02
A3	-	-	0.203
b	0.24	0.34	0.29
D	2.95	3.05	3.00
D2	0.84	1.04	0.94
e	-	-	0.65
E	1.95	2.05	2.00
E2	0.70	0.90	0.80
L	0.27	0.37	0.32
L1	0.15	0.25	0.20
K	-	-	0.68
Z	-	-	0.38
<b>All Dimensions in mm</b>			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

### V-DFN3020-8 (Type N)



Dimensions	Value (in mm)
C	0.650
G	0.580
X	0.390
X1	1.040
X2	2.340
Y	0.520
Y1	0.900
Y2	0.300
Y3	2.300

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